

BAT54SWT1

Preferred Device

Dual Series Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 Volts (Typ) @ $I_F = 10 \text{ mA}$

MAXIMUM RATINGS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

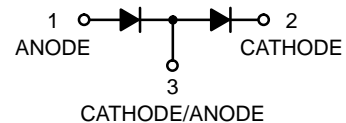
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Volts
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_F	200 1.6	mW mW/ $^\circ\text{C}$
Forward Current (DC)	I_F	200 Max	mA
Junction Temperature	T_J	125 Max	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$



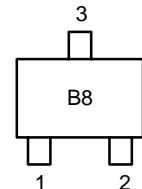
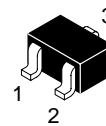
ON Semiconductor™

<http://onsemi.com>

30 VOLT DUAL SERIES SCHOTTKY BARRIER DIODES



MARKING DIAGRAM



(SC-70)
SOT-323
CASE 419
STYLE 9

ORDERING INFORMATION

Device	Package	Shipping
BAT54SWT1	SOT-323	3000/Tape & Reel

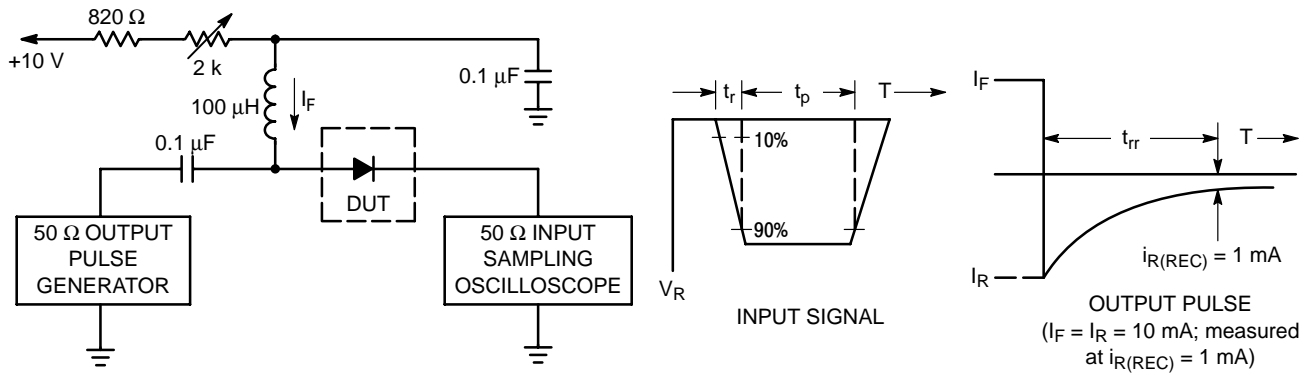
Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	30	–	–	Volts
Total Capacitance ($V_R = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	–	7.6	10	pF
Reverse Leakage ($V_R = 25 \text{ V}$)	I_R	–	0.5	2.0	μA dc
Forward Voltage ($I_F = 0.1 \text{ mA}$ dc)	V_F	–	0.22	0.24	Vdc
Forward Voltage ($I_F = 30 \text{ mA}$ dc)	V_F	–	0.41	0.5	Vdc
Forward Voltage ($I_F = 100 \text{ mA}$ dc)	V_F	–	0.52	0.8	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}$ dc, $I_{R(REC)} = 1.0 \text{ mA}$ dc, Figure 1)	t_{rr}	–	–	5.0	ns
Forward Voltage ($I_F = 1.0 \text{ mA}$ dc)	V_F	–	0.29	0.32	Vdc
Forward Voltage ($I_F = 10 \text{ mA}$ dc)	V_F	–	0.35	0.40	Vdc
Forward Current (DC)	I_F	–	–	200	mA
Repetitive Peak Forward Current	I_{FRM}	–	–	300	mA
Non–Repetitive Peak Forward Current ($t < 1.0 \text{ s}$)	I_{FSM}	–	–	600	mA

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- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

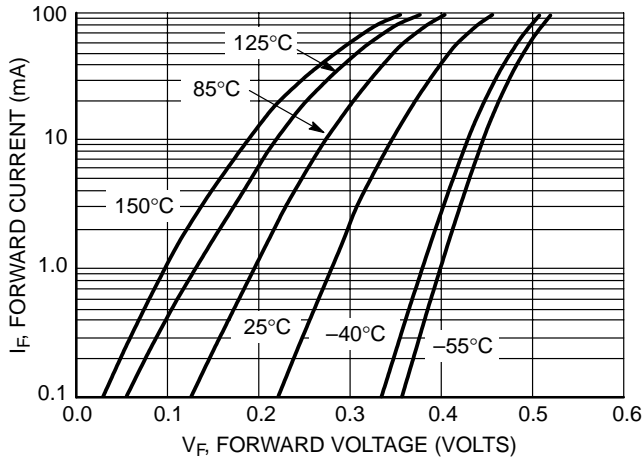


Figure 2. Forward Voltage

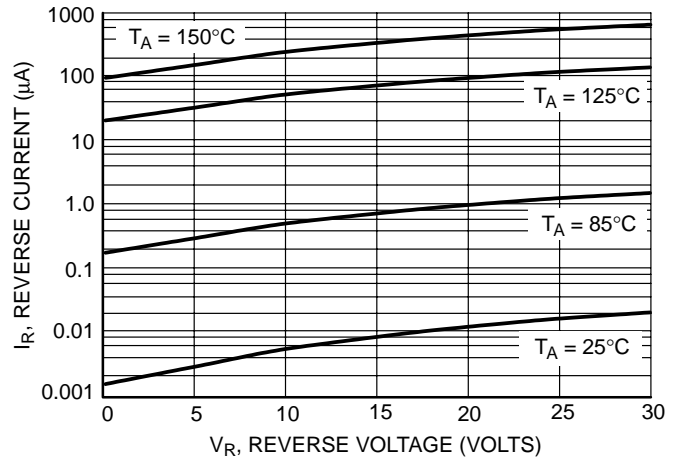


Figure 3. Leakage Current

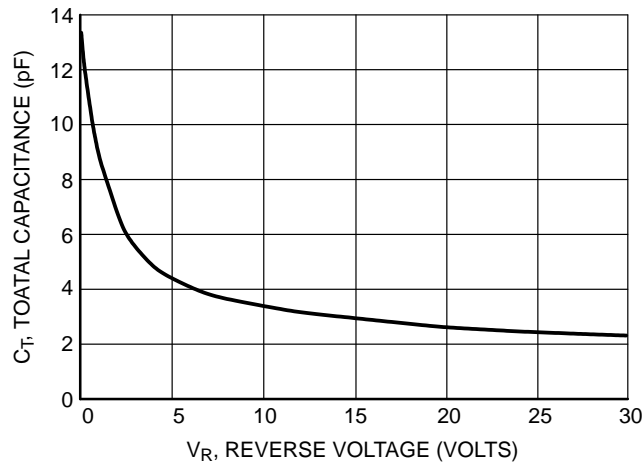


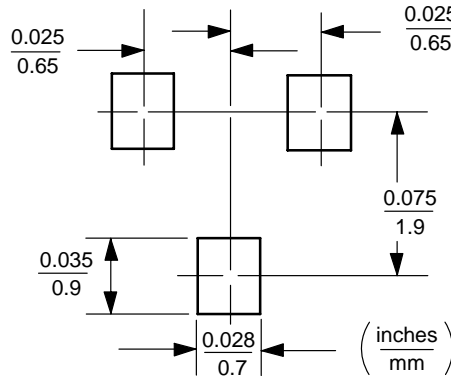
Figure 4. Total Capacitance

INFORMATION FOR USING THE SOT-323 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SC-70/SOT-323 POWER DISSIPATION

The power dissipation of the SC-70/SOT-323 is a function of the collector pad size. This can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient; and the operating temperature, T_A . Using the values provided on the data sheet, P_D can be calculated as follows.

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 200 milliwatts.

$$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{625^\circ\text{C/W}} = 200 \text{ milliwatts}$$

The 625°C/W assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 200 milliwatts. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, a power dissipation of 300 milliwatts can be achieved using the same footprint.

SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

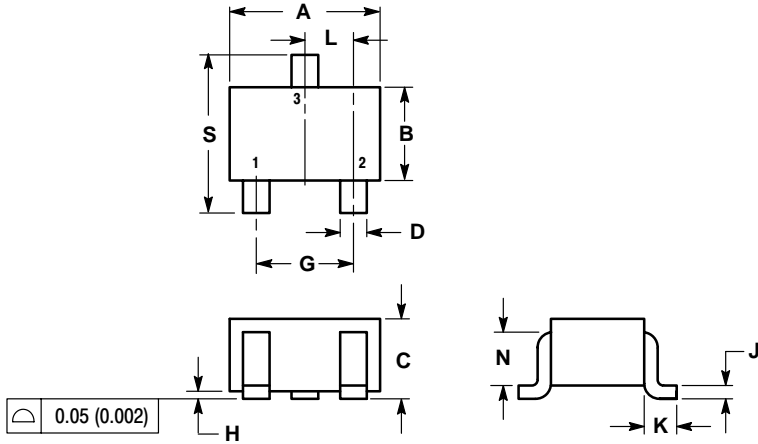
- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.
- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling

* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

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PACKAGE DIMENSIONS

(SC-70)
SOT-323
PLASTIC PACKAGE
CASE 419-02
ISSUE H



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40


- STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

Notes

Notes

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